

Product data sheet

1. General description

Hyperfast power diode in a SOD59 (2-lead TO-220AC) plastic package.

2. Features and benefits

- · Low reverse recovery current and low thermal resistance
- Reduces switching losses in associated MOSFET

3. Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies
- Half-bridge lighting ballasts

4. Quick reference data

Table 1. Quic	k reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	-	600	V
I _{F(AV)}	average forward current	δ = 0.5; T _{mb} ≤ 109 °C; square-wave pulse; Fig. 1; Fig. 2	-	-	8	A
Static chara	cteristics					
V _F	forward voltage	I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u>	-	1.4	1.85	V
Dynamic ch	aracteristics					
t _{rr}	reverse recovery time	$I_{F} = 8 \text{ A}; \text{ V}_{R} = 400 \text{ V}; \text{ d}_{F}/\text{d}t = 500 \text{ A}/\mu\text{s}; \\ T_{j} = 25 \text{ °C}; \frac{\text{Fig. 5}}{2}$	-	19	-	ns

5. Pinning information

Table 2.	Pinning in	formation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode	mb	K — K — A
2	А	anode		001aaa020
mb	mb	mounting base; cathode	C C C C C C C C C C C C C C C C C C C	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BYC8-600	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59		

BYC8-600

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	600	V
V _{RWM}	crest working reverse voltage		-	600	V
I _{F(AV)}	average forward current	δ = 0.5; T _{mb} ≤ 109 °C; square-wave pulse; <u>Fig. 1</u> ; <u>Fig. 2</u>	-	8	A
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 µs; T _{mb} ≤ 109 °C; square-wave pulse	-	16	A
I _{FSM}	non-repetitive peak	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	-	80	А
	forward current	t _p = 8.3 ms; T _{j(init)} = 25 °C; sine-wave pulse	-	88	A
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

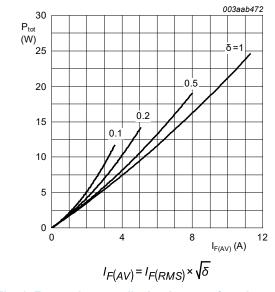


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

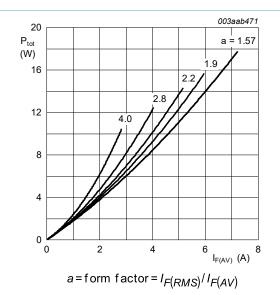


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

Hyperfast power diode

8. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 3	-	-	2.2	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air		-	60	-	K/W

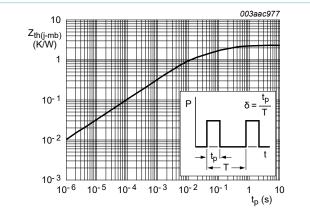
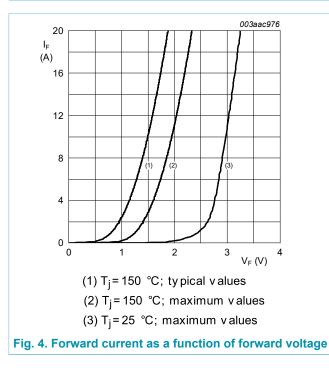


Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse width

Hyperfast power diode

9. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _F	forward voltage	I _F = 8 A; T _j = 25 °C	-	2	2.9	V
		I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u>	-	1.4	1.85	V
		I _F = 16 A; T _j = 150 °C	-	1.7	2.3	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	9	150	μA
		V _R = 600 V; T _j = 100 °C	-	1.1	3	mA
Dynamic ch	aracteristics					
t _{rr}	reverse recovery time	I_F = 1 A; V _R = 30 V; dI _F /dt = 50 A/µs; T _j = 25 °C; <u>Fig. 5</u>	-	30	52	ns
		I_F = 8 A; V _R = 400 V; dI _F /dt = 500 A/µs; T _j = 25 °C; <u>Fig. 5</u>	-	19	-	ns
		I_F = 8 A; V _R = 400 V; dI _F /dt = 500 A/µs; T _j = 100 °C; <u>Fig. 5</u>	-	32	40	ns
I _{RM}	peak reverse recovery current	I_{F} = 8 A; V_{R} = 400 V; dI_{F}/dt = 50 A/µs; T_{j} = 125 °C	-	1.5	5.5	A
		$I_{\rm F}$ = 8 A; $V_{\rm R}$ = 400 V; dI_F/dt = 500 A/µs; $T_{\rm j}$ = 100 °C	-	9.5	12	A
Q _r	recovered charge	I_{F} = 1 A; V_{R} = 100 V; dI_{F}/dt = 100 A/µs; T_{j} = 25 °C	-	12	-	nC
V _{FR}	forward recovery voltage	I _F = 10 A; dI _F /dt = 100 A/μs; T _j = 25 °C; Fig. 6	-	8	10	V



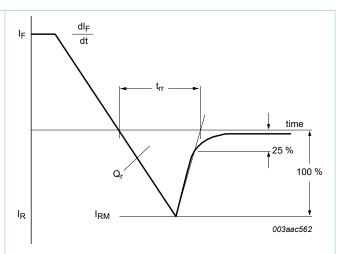


Fig. 5. Reverse recovery definitions; ramp recovery

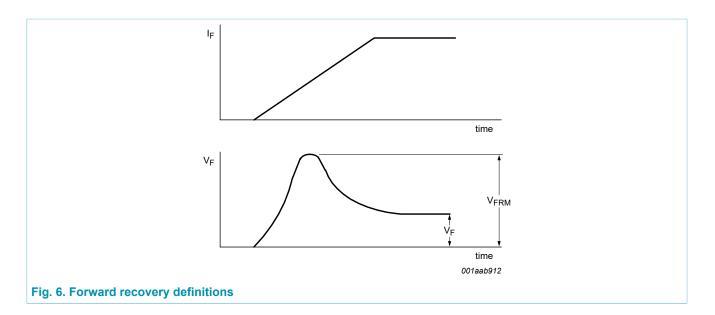
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BYC8-600

Hyperfast power diode



BYC8-600

10. Package outline

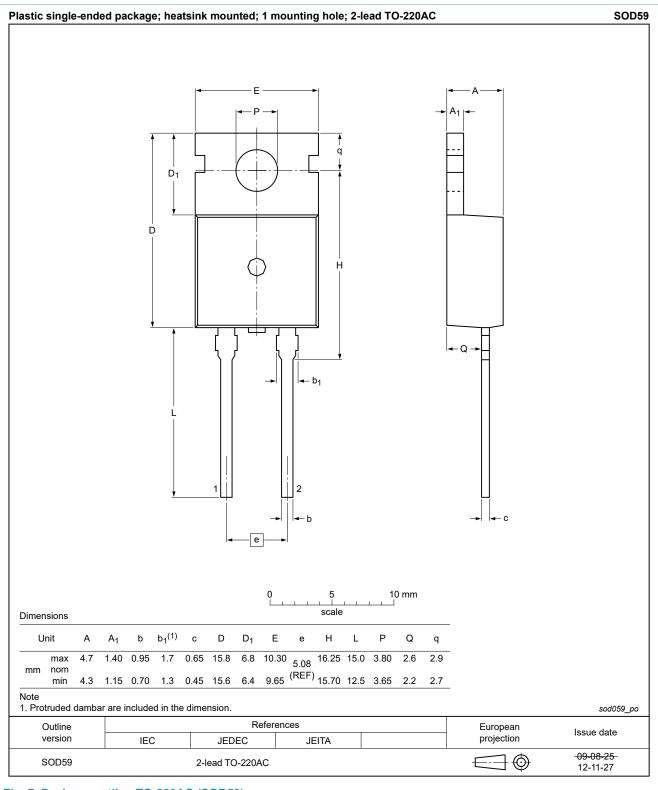


Fig. 7. Package outline TO-220AC (SOD59)

BYC8-600

Hyperfast power diode

11. Legal information

Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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